

thickness larger than that of the second insulating film;

forming a groove in a region of said third insulating film, in which a wiring is to be formed, ~~said groove having a bottom to which said second insulating film is exposed~~; and

forming a metal wiring in said groove.

Claim 29, line 1, after "removing" insert --a part of--.

Please add the following new claims:

--40. A process of fabricating a semiconductor device comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a second insulating film on said first insulating film, said second insulating film being made of a material different from that of the first insulating film and having a thickness smaller than that of the first insulating film;

forming a third insulating film on said second insulating film, said third insulating film being made of a material different from that of the second insulating film and having a thickness larger than that of the second insulating film;

forming a groove in said third insulating film having a bottom comprising said second insulating film; and

forming a wiring material in said groove.

41. The process according to claim 28, wherein said step of forming said groove comprises:

removing a first portion of said second insulation film to expose said third insulation film while leaving a remaining second portion of said second insulation film; and

removing a third portion of said first insulation film to expose said substrate while leaving a remaining fourth portion of said third insulation film.--